The 18th International Conference on Crystal Growth and Epitaxy

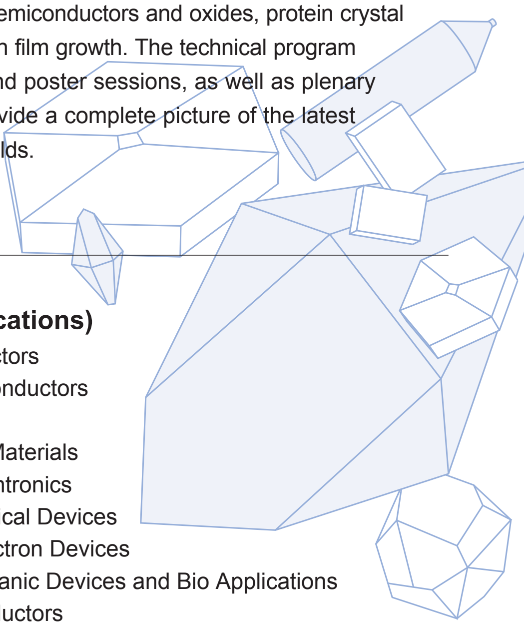
ICCGE-18

Nagoya, Japan

August 7th - 12th, 2016

ICCGE-18
ISSCG-16

On behalf of organizing committee, we are honored to welcome all of you to join in the 18th International Conference on Crystal Growth and Epitaxy (ICCGE-18). Our theme of this conference is “Opening up the Future of Crystal Growth based on Fundamentals”. Spirit of the theme is to create new concepts and technologies by collaboration between basic science and engineering. To realize the idea, ICCGE-18 will provide sessions of the presentation and the discussion regarding the recent research and development activities in all aspects of crystal growth. The conference is consisted of the topical and general sessions. The topical sessions are planned for nanostructure fabrication, magnetic semiconductors, wide-bandgap semiconductors and other topics, while the general sessions may contain theory of crystal growth, pattern formation, bulk crystal growth of semiconductors and oxides, protein crystal growth and epitaxial thin film growth. The technical program will include both oral and poster sessions, as well as plenary and invited talks to provide a complete picture of the latest developments in the fields.



Category Plan [Tentative]

General Session
(Fundamentals & Growth Technologies)

- **G01** Fundamentals of Nucleation and Crystal Growth
- **G02** Surfaces and Interfaces
- **G03** Nanomaterials and Low Dimensional Structures
- **G04** Thin Films and Epitaxial Growth
- **G05** Organic and Biological Crystallization
- **G06** Bulk Crystal Growth
- **G07** Crystalline Defect
- **G08** Advanced Growth Technologies
- **G09** In situ Observation and Characterization
- **G10** External Fields, Microgravity
- **G11** Industrial Crystallization

Topical Session
(Materials & Applications)

- **T01** III-V Semiconductors
- **T02** Group IV Semiconductors
- **T03** 2D Materials
- **T04** II-VI and Oxide Materials
- **T05** Materials for Spintronics
- **T06** Materials for Optical Devices
- **T07** Materials for Electron Devices
- **T08** Materials for Organic Devices and Bio Applications
- **T09** Nitride Semiconductors
- **T10** SiC
- **T11** Late News Session

Joint Session - examples -

Growth Simulation and Practice
Nanostructure - Fundamentals and Applications

Proceedings

The proceedings of the conference will be published as a special issue of Journal of Crystal Growth (JCG).

Organizing Committee

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